

75V NPN MEDIUM POWER HIGH GAIN TRANSISTOR IN SOT223

Features

- BV_{CEO} > 75V
- I_C= 4.5A High Continuous Collector Current
- I_{CM} = 10A Peak Pulse Current
- Low Saturation Voltage V_{CE(sat)} < 120mV @ 1A
- hFE > 300 @ I_C=1A for a High Gain Hold-Up
- $R_{CE(sat)}$ = 78m Ω at 4.5A for a Low Equivalent On-Resistance
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

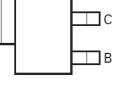
Mechanical Data

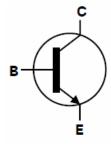
Case: SOT223

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- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.112 grams (Approximate)







Equivalent Circuit

Ordering Information (Note 4)

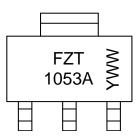
Part Number	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
FZT1053ATA	AEC-Q101	FZT1053A	7	12	1.000

Pin Out

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen and Antimony free, "Green" and Lead-Free.
- 3. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information

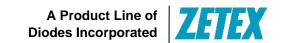


SOT223

FZT 1053A = Product Type Marking Code YWW = Date Code Marking Y or \overline{Y} = Last Digit of Year (ex: 5= 2015) WW or $\overline{W}W = Week Code (01~53)$

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Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	150	V
Collector-Emitter Voltage	V _{CEO}	75	V
Emitter-Base Voltage	V _{EBO}	7.0	V
Continuous Collector Current	Ic	4.5	Α
Base Current	I _B	500	mA
Peak Pulse Current	I _{CM}	10	Α

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
	(Note 5)		3.0		
Power Dissipation	(Note 6)		2.0	W	
Power Dissipation	(Note 7)	P_D	1.6] vv	
	(Note 8)		1.2		
	(Note 5)		41.7		
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{ hetaJA}$	62.5		
Thermal Resistance, Junction to Ambient	(Note 7)		78.1	°C/W	
	(Note 8)		104		
Thermal Resistance Junction to Lead (Note 9)		$R_{ heta JL}$	10.9		
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C		

ESD Ratings (Note 7)

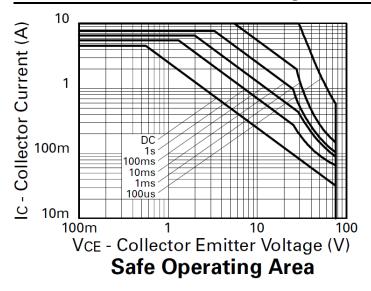
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

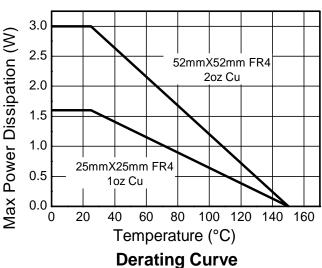
Notes:

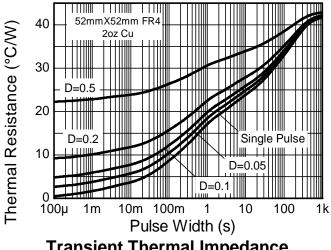
- 5. For a device mounted with the collector lead on 52mm x 52mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
- 6. Same as Note 5, except the device is mounted on 25mm x 25mm 2oz copper.
- 7. Same as Note 5, except the device is mounted on 25mm x 25mm 1oz copper.
- 8. Same as Note 5, except the device is mounted on minimum recommended pad layout.
- 9. Thermal resistance from junction to solder-point (at the end of the collector lead).
- 10. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

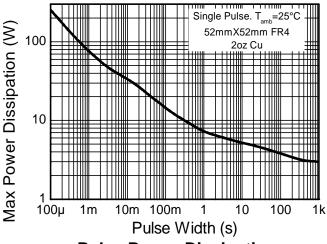


Thermal Characteristics and Derating Information





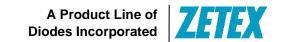




Transient Thermal Impedance

Pulse Power Dissipation





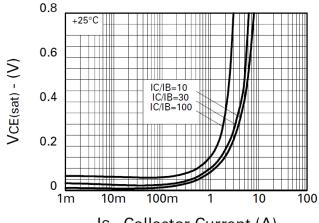
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур.	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	150	250	-	V	$I_{C} = 100 \mu A$
Collector-Emitter Breakdown Voltage	BV _{CES}	150	250	-	V	$I_{C} = 100 \mu A$
Collector-Emitter Breakdown Voltage (Note 11)	BV_{CEO}	75	100	-	V	$I_C = 10mA$
Collector-Emitter Breakdown Voltage	BV_CEV	150	250	-	V	$I_C = 100 \mu A, V_{EB} = 1 V$
Emitter-Base Breakdown Voltage	BV_{EBO}	7.0	8.8	-	V	$I_E = 100 \mu A$
Collector Cutoff Current	I _{CBO}	-	0.9	10	nA	V _{CB} = 120V
Collector Cutoff Current	I _{CES}	-	1.5	10	nA	V _{CES} = 120V
Emitter Cutoff Current	I _{EBO}	-	0.3	10	nA	$V_{EB} = 4V$
		270	440	-	-	$I_C = 10mA$, $V_{CE} = 2V$
	h _{FE}	300	450	1,200		$I_C = 0.5A, V_{CE} = 2V$
DC current transfer Static Ratio (Note 11)		300	450	-		$I_C = 1A$, $V_{CE} = 2V$
		40	60	-		I _C = 4.5A, V _{CE} = 2V
		-	20	-		I _C = 10A, V _{CE} = 2V
		-	21	30	mV	$I_C = 0.2A$, $I_B = 20mA$
	VCE(sat)	-	55	75		$I_C = 0.5A, I_B = 20mA$
Collector-Emitter Saturation Voltage (Note 11)		-	150	200		$I_C = 1A$, $I_B = 10mA$
		-	160	210		$I_C = 2A$, $I_B = 100mA$
		-	350	440		$I_C = 4.5A, I_B = 200mA$
Base-Emitter Saturation Voltage (Note 11)	V _{BE(sat)}	-	900	1,000	mV	$I_C = 3A$, $I_B = 100mA$
Base-Emitter Turn-On Voltage (Note 11)	$V_{BE(on)}$	-	825	950	mV	$I_C = 3A$, $V_{CE} = 2V$
Transitional Frequency (Note 11)	f_{T}	-	140	-	MHz	$I_C = 50 \text{mA}, V_{CE} = 10 \text{V},$ f = 100 MHz
Output Capacitance	C _{obo}	-	21	30	pF	$V_{CB} = 10V, f = 1MHz,$
Switching Time	t _{on}	-	162	-	ns	$V_{CC} = 50V, I_C = 2A,$
Switching Time	t _{off}	-	900	-	ns	$I_{B1} = I_{B2} = \pm 20 \text{mA}$

Note: 11. Measured under pulsed conditions. Pulse width = $300\mu s$. Duty cycle $\leq 2\%$.

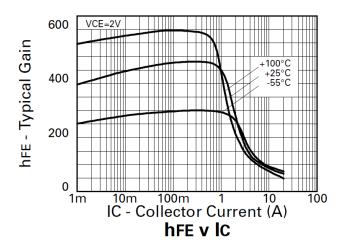


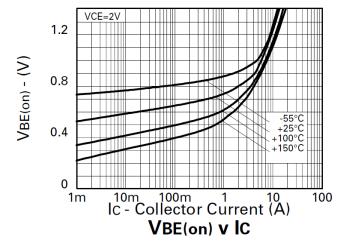
Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

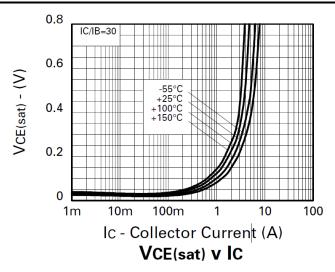


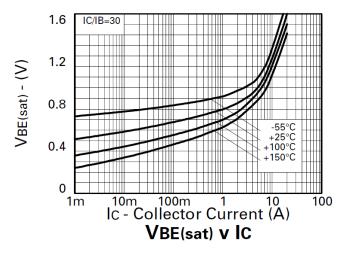
Ic - Collector Current (A)

VCE(sat) v IC





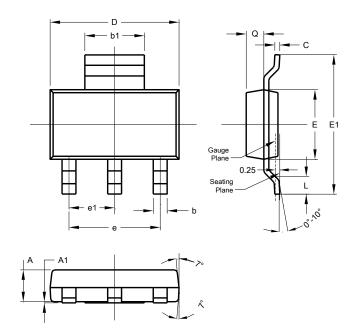






Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

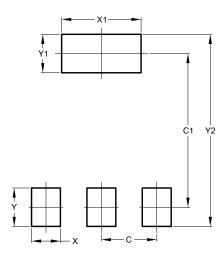


SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b	0.60	0.80	0.70		
b1	2.90	3.10	3.00		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
Е	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	-	-	4.60		
e1	-	-	2.30		
L	0.85	1.05	0.95		
Q	0.84	0.94	0.89		
All Dimensions in mm					

Suggested Pad Layout

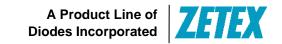
Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.

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Dimensions	Value (in mm)		
C	2.30		
C1	6.40		
Х	1.20		
X1	3.30		
Y	1.60		
Y1	1.60		
Y2	8.00		





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